Eva Monroy

List of Publications by Year
in descending order

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386 papers	10,548 citations	38742 50 h-index	49909 87 g-index
388 all docs	388 docs citations	388 times ranked	6859 citing authors

#	Article	IF	Citations
1	Thermally propagated Al contacts on SiGe nanowires characterized by electron beam induced current in a scanning transmission electron microscope. Nanotechnology, 2022, 33, 035712.	2.6	0
2	Electron beam pumped light emitting devices. Journal Physics D: Applied Physics, 2022, 55, 273003.	2.8	5
3	The Role of the Built-In Electric Field in Recombination Processes of GaN/AlGaN Quantum Wells: Temperature- and Pressure-Dependent Study of Polar and Non-Polar Structures. Materials, 2022, 15, 2756.	2.9	1
4	Reduction of the lasing threshold in optically pumped AlGaN/GaN lasers with two-step etched facets. Semiconductor Science and Technology, 2022, 37, 075013.	2.0	2
5	Solubility Limit of Ge Dopants in AlGaN: A Chemical and Microstructural Investigation Down to the Nanoscale. ACS Applied Materials & Interfaces, 2021, 13, 4165-4173.	8.0	7
6	Improvement of critical temperature of niobium nitride deposited on 8-inch silicon wafers thanks to an AlN buffer layer. Superconductor Science and Technology, 2021, 34, 045002.	3.5	4
7	Study of AlxGa1-xN/AlN (0 â‰ x â‰ 0.1) quantum dots for the fabrication of E-beam pumped UV emitters. , 2021, , .		1
8	Development of AlGaN/GaN heterostructures for e-beam pumped UV lasers. , 2021, , .		1
9	AlGaN/GaN asymmetric graded-index separate confinement heterostructures designed for electron-beam pumped UV lasers. Optics Express, 2021, 29, 13084.	3.4	5
10	Electron beam induced current microscopy of silicon pâ€“n junctions in a scanning transmission electron microscope. Journal of Applied Physics, 2021, 129, .	2.5	8
11	Sub-250Âfs passively mode-locked ultralong ring fibre oscillators. Optics and Laser Technology, 2021, 138, 106848.	4.6	7
12	Critical Evaluation of Various Spontaneous Polarization Models and Induced Electric Fields in III-Nitride Multi-Quantum Wells. Materials, 2021, 14, 4935.	2.9	6
13	Performance enhancement of an ultrafast all-fiber laser based on an InN saturable absorber using GRIN coupling. Optics Express, 2021, 29, 29357.	3.4	6
14	Non-polar GaN/AlGaN quantum-well polariton laser at room temperature. Physical Review B, 2021, 104, .	3.2	2
15	Decorrelation of internal quantum efficiency and lasing threshold in AlGaN-based separate confinement heterostructures for UV emission. Applied Physics Letters, 2021, 119, 151103.	3.3	2
16	High energy ultrafast all-fiber laser based on InN-GRIN saturable absorber. , 2021, , .		0
17	Design of AlGaN/AlN Dotâ€inâ€aâ€Wire Heterostructures for Electronâ€Pumped UV Emitters. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900714.	1.8	4
18	Intersubband transitions in GaN-based heterostructures. , 2020, , 539-565.		0

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19	Correlated Electro-Optical and Structural Study of Electrically Tunable Nanowire Quantum Dot Emitters. Nano Letters, 2020, 20, 314-319.	9.1	3
20	InGaN Quantum Dots Studied by Correlative Microscopy Techniques for Enhanced Light-Emitting Diodes. ACS Applied Nano Materials, 2020, 3, 10133-10143.	5.0	5
21	High-Quality, InN-Based, Saturable Absorbers for Ultrafast Laser Development. Applied Sciences (Switzerland), 2020, 10, 7832.	2.5	4
22	Wurtzite quantum well structures under high pressure. Journal of Applied Physics, 2020, 128, .	2.5	4
23	UV Emission from GaN Wires with m-Plane Coreâ€“Shell GaN/AlGaN Multiple Quantum Wells. ACS Applied Materials & Interfaces, 2020, 12, 44007-44016.	8.0	16
24	Multi-microscopy nanoscale characterization of the doping profile in a hybrid Mg/Ge-doped tunnel junction. Nanotechnology, 2020, 31, 465706.	2.6	6
25	Hydrostatic pressure dependence of indirect and direct excitons in InGaN/GaN quantum wells. Physical Review B, 2020, 101, .	3.2	6
26	Correlated and in-situ electrical transmission electron microscopy studies and related membrane-chip fabrication. Nanotechnology, 2020, 31, 472001.	2.6	8
27	Transferrable dielectric DBR membranes for versatile GaN-based polariton and VCSEL technology. Microelectronic Engineering, 2020, 228, 111276.	2.4	2
28	Instantaneous decay rate analysis of time resolved photoluminescence (TRPL): Application to nitrides and nitride structures. Journal of Alloys and Compounds, 2020, 823, 153791.	5.5	5
29	Detection of Si doping in the AlN/GaN MQW using Super X â€“ EDS measurements. Micron, 2020, 134, 102864.	2.2	3
30	Assessment of AlGaN/AlN superlattices on GaN nanowires as active region of electron-pumped ultraviolet sources. Nanotechnology, 2020, 31, 204001.	2.6	14
31	Internal quantum efficiency of AlGaN/AlN quantum dot superlattices for electron-pumped ultraviolet sources. Nanotechnology, 2020, 31, 505205.	2.6	6
32	Effect of Bias on the Response of GaN Axial pâ€“n Junction Single-Nanowire Photodetectors. Nano Letters, 2019, 19, 5506-5514.	9.1	31
33	Novel InN-Based SESAMs with Ultra-Short Time Response. , 2019, , .		0
34	Absorption in ultrathin GaN-based membranes: The role of standing wave effects. Journal of Applied Physics, 2019, 126, 083109.	2.5	2
35	Electrical and optical properties of heavily Ge-doped AlGaN. Journal Physics D: Applied Physics, 2019, 52, 125101.	2.8	22
36	On intrinsic Stokes shift in wide GaN/AlGaN polar quantum wells. Semiconductor Science and Technology, 2019, 34, 075021.	2.0	1

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37	Design and implementation of bound-to-quasibound GaN/AlGaN photovoltaic quantum well infrared photodetectors operating in the short wavelength infrared range at room temperature. Journal of Applied Physics, 2019, 125, 174505.	2.5	10
38	Nanowire photodetectors based on wurtzite semiconductor heterostructures. Semiconductor Science and Technology, 2019, 34, 053002.	2.0	24
39	Improved GaN Quantum Well Microcavities for Robust Room Temperature Polaritonics. Physica Status Solidi (B): Basic Research, 2019, 256, 1800716.	1.5	5
40	Megawatt Peak-Power Femtosecond Ultralong Ring Fibre Laser with InN SESAM. , 2019, , .		1
41	Improvement of the critical temperature of NbTiN films on III-nitride substrates. Superconductor Science and Technology, 2019, 32, 035008.	3.5	10
42	Near- and mid-infrared intersubband absorption in top-down GaN/AlN nano- and micro-pillars. Nanotechnology, 2019, 30, 054002.	2.6	5
43	Effect of the residual doping on the performance of InN epilayers as saturable absorbers for ultrafast lasers at 155Âµm. Optical Materials Express, 2019, 9, 2785.	3.0	2
44	Ultrafast Fiber Laser Using InN as Saturable Absorber Mirror. Journal of Lightwave Technology, 2018, 36, 2175-2182.	4.6	11
45	Effect of the nanowire diameter on the linearity of the response of GaN-based heterostructured nanowire photodetectors. Nanotechnology, 2018, 29, 255204.	2.6	15
46	In situbiasing and off-axis electron holography of a ZnO nanowire. Nanotechnology, 2018, 29, 025710.	2.6	10
47	Advanced Superconducting Nanowire Single Photon Detectors for Photonic Quantum Technologies. Proceedings (mdpi), 2018, 2, .	0.2	0
48	GaN/AlGaN Photovoltaic Quantum Well Infrared Photodetector at 2.3 Î¼m. , 2018, , .		0
49	Switching of exciton character in double InGaN/GaN quantum wells. Physical Review B, 2018, 98, .	3.2	16
50	Intersubband absorption in GaN nanowire heterostructures at mid-infrared wavelengths. Nanotechnology, 2018, 29, 385201.	2.6	5
51	Polarization-insensitive fiber-coupled superconducting-nanowire single photon detector using a high-index dielectric capping layer. Optics Express, 2018, 26, 17697.	3.4	14
52	Infrared emitters using III-nitride semiconductors. , 2018, , 587-617.		3
53	Quality improvement of AlInN/p-Si heterojunctions with AlN buffer layer deposited by RF-sputtering. Journal of Alloys and Compounds, 2018, 769, 824-830.	5.5	15
54	Experimental and theoretical analysis of influence of barrier composition on optical properties of GaN/AlGaN multi-quantum wells: Temperature- and pressure-dependent photoluminescence studies. Journal of Alloys and Compounds, 2018, 769, 1064-1071.	5.5	9

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55	Study of Absorption Saturation in InN Thin Films through the Z-Scan Technique at 1.55 Î¼m. , 2018, , .		0
56	Development of AlInN photoconductors deposited by sputtering. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1600780.	1.8	0
57	High absorption efficiency and polarization-insensitivity in superconducting-nanowire single-photon detectors. Proceedings of SPIE, 2017, , .	0.8	0
58	Experimental and first-principles studies of high-pressure effects on the structural, electronic, and optical properties of semiconductors and lanthanide doped solids. Japanese Journal of Applied Physics, 2017, 56, 05FA02.	1.5	7
59	P-i-n InGaN homojunctions (10â€“40% In) synthesized by plasma-assisted molecular beam epitaxy with extended photoresponse to 600 nm. Solar Energy Materials and Solar Cells, 2017, 160, 355-360.	6.2	14
60	Design of polarization-insensitive superconducting single photon detectors with high-index dielectrics. Superconductor Science and Technology, 2017, 30, 035005.	3.5	16
61	Bias-Controlled Spectral Response in GaN/AlN Single-Nanowire Ultraviolet Photodetectors. Nano Letters, 2017, 17, 4231-4239.	9.1	45
62	Short-wave infrared (Î»â€‰=â€‰3â€‰Î¼m) intersubband polaritons in the GaN/AlN system. Applied Physics Letters, 2017, 110, .	3.3	12
63	Ab initio and experimental studies of polarization and polarization related fields in nitrides and nitride structures. AIP Advances, 2017, 7, .	1.3	23
64	Intersubband absorption in Siâ€•and Geâ€doped GaN/AlN heterostructures in selfâ€assembled nanowire and 2D layers. Physica Status Solidi (B): Basic Research, 2017, 254, 1600734.	1.5	16
65	Effect of Al incorporation in nonpolar m -plane GaN/AlGaN multi-quantum-wells using plasma-assisted molecular-beam epitaxy. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1600849.	1.8	6
66	In-rich Al_xIn_{1â^’x}N grown by RF-sputtering on sapphire: from closely-packed columnar to high-surface quality compact layers. Journal Physics D: Applied Physics, 2017, 50, 065101.	2.8	15
67	Near-Infrared Intersubband Photodetection in GaN/AlN Nanowires. Nano Letters, 2017, 17, 6954-6960.	9.1	33
68	Effect of Ge-doping on the short-wave, mid- and far-infrared intersubband transitions in GaN/AlGaN heterostructures. Semiconductor Science and Technology, 2017, 32, 125002.	2.0	6
69	Gallium kinetics on m-plane GaN. Applied Physics Letters, 2017, 111, .	3.3	11
70	Ultra-low threshold polariton lasing at room temperature in a GaN membrane microcavity with a zero-dimensional trap. Scientific Reports, 2017, 7, 5542.	3.3	23
71	Bias-Controlled Optical Transitions in GaN/AlN Nanowire Heterostructures. ACS Nano, 2017, 11, 8758-8767.	14.6	10
72	Effect of doping on the intersubband absorption in Si- and Ge-doped GaN/AlN heterostructures. Nanotechnology, 2017, 28, 405204.	2.6	24

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73	Carrier Localization in GaN/AlN Quantum Dots As Revealed by Three-Dimensional Multimicroscopy. Nano Letters, 2017, 17, 4261-4269.	9.1	14
74	Multi-excitonic emission from Stranski-Krastanov GaN/AlN quantum dots inside a nanoscale tip. Applied Physics Letters, 2017, 111, .	3.3	11
75	Sub-250 fs, 650 kW Peak Power Harmonic Mode-Locked Fiber Laser with InN-based SESAM. , 2017, , .		1
76	Widely power-tunable polarization-independent ultrafast mode-locked fiber laser using bulk InN as saturable absorber. Optics Express, 2017, 25, 5366.	3.4	12
77	Sub-200 fs mode-locked fiber laser with InN-based SESAM. , 2017, , .		1
78	Intersubband Optoelectronics Using III-Nitride Semiconductors. Series in Optics and Optoelectronics, 2017, , 615-644.	0.0	1
79	A New Ultrafast and High Peak Power Fiber Laser operating at 1.5 Âµm using InN as Saturable Absorber. , 2017, , .		0
80	Nitride-Based Devices at Telecom Wavelengths. , 2017, , .		1
81	Design of broadband high-efficiency superconducting-nanowire single photon detectors. Superconductor Science and Technology, 2016, 29, 065016.	3.5	43
82	High pressure and time resolved studies of optical properties of n-type doped GaN/AlN multi-quantum wells: Experimental and theoretical analysis. Journal of Applied Physics, 2016, 120, .	2.5	14
83	Short-wavelength, mid- and far-infrared intersubband absorption in nonpolar GaN/Al(Ga)N heterostructures. Japanese Journal of Applied Physics, 2016, 55, 05FG05.	1.5	9
84	Dependence of the photovoltaic performance of pseudomorphic InGaN/GaN multiple-quantum-well solar cells on the active region thickness. Applied Physics Letters, 2016, 108, .	3.3	24
85	Correlation of optical and structural properties of GaN/AlN multi-quantum wellsâ€" Ab initio and experimental study. Journal of Applied Physics, 2016, 119, 015703.	2.5	27
86	Impact of recess etching and surface treatments on ohmic contacts regrown by molecular-beam epitaxy for AlGaN/GaN high electron mobility transistors. Applied Physics Letters, 2016, 109, .	3.3	22
87	Ge doping of GaN beyond the Mott transition. Journal Physics D: Applied Physics, 2016, 49, 445301.	2.8	36
88	Study of high In-content AlInN deposition on p-Si(111) by RF-sputtering. Japanese Journal of Applied Physics, 2016, 55, 05FB07.	1.5	16
89	UV Photosensing Characteristics of Nanowire-Based GaN/AlN Superlattices. Nano Letters, 2016, 16, 3260-3267.	9.1	53
90	Composition Analysis of III-Nitrides at the Nanometer Scale: Comparison of Energy Dispersive X-ray Spectroscopy and Atom Probe Tomography. Nanoscale Research Letters, 2016, 11, 461.	5.7	17

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91	IIIâ€nitrideâ€based waveguides for ultrafast allâ€optical signal processing at 1.55 Î¼m. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 1269-1275.	1.8	2
92	Effect of doping on the far-infrared intersubband transitions in nonpolarm-plane GaN/AlGaN heterostructures. Nanotechnology, 2016, 27, 145201.	2.6	16
93	Morphology and arrangement of InN nanocolumns deposited by radio-frequency sputtering: Effect of the buffer layer. Journal of Crystal Growth, 2016, 434, 13-18.	1.5	14
94	Long-lived excitons in GaN/AlN nanowire heterostructures. Physical Review B, 2015, 91, .	3.2	17
95	Nonpolarm-plane GaN/AlGaN heterostructures with intersubband transitions in the 5â€“10 THz band. Nanotechnology, 2015, 26, 435201.	2.6	26
96	Effect of the barrier thickness on the performance of multiple-quantum-well InGaN photovoltaic cells. Japanese Journal of Applied Physics, 2015, 54, 072302.	1.5	19
97	Intersubband transitions in nonpolar GaN/Al(Ga)N heterostructures in the short- and mid-wavelength infrared regions. Journal of Applied Physics, 2015, 118, 014309.	2.5	26
98	Infrared emitters made from III-nitride semiconductors. , 2014, , 533-565.		4
99	High In-content InGaN layers synthesized by plasma-assisted molecular-beam epitaxy: Growth conditions, strain relaxation, and In incorporation kinetics. Journal of Applied Physics, 2014, 116, .	2.5	36
100	Alloy inhomogeneity and carrier localization in AlGaN sections and AlGaN/AlN nanodisks in nanowires with 240â€“350â€‰nm emission. Applied Physics Letters, 2014, 105, .	3.3	34
101	Effect of the quantum well thickness on the performance of InGaN photovoltaic cells. Applied Physics Letters, 2014, 105, .	3.3	60
102	High Precision, Electrochemical Detection of Reversible Binding of Recombinant Proteins on Wide Bandgap GaN Electrodes Functionalized with Biomembrane Models. Advanced Functional Materials, 2014, 24, 4927-4934.	14.9	4
103	Enhanced room-temperature mid-ultraviolet emission from AlGaN/AlN Stranski-Krastanov quantum dots. Journal of Applied Physics, 2014, 116, 023502.	2.5	14
104	Ultra-smooth GaN membranes by photo-electrochemical etching for photonic applications. Journal of Materials Science, 2014, 49, 4018-4024.	3.7	11
105	THz intersubband transitions in AlGaN/GaN multiâ€quantumâ€wells. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 761-764.	1.8	11
106	Pseudo-square AlGaN/GaN quantum wells for terahertz absorption. Applied Physics Letters, 2014, 105, 131106.	3.3	25
107	Intraband Absorption in Self-Assembled Ge-Doped GaN/AlN Nanowire Heterostructures. Nano Letters, 2014, 14, 1665-1673.	9.1	33
108	Improved conversion efficiency of as-grown InGaN/GaN quantum-well solar cells for hybrid integration. Applied Physics Express, 2014, 7, 032301.	2.4	18

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109	High-quality NbN nanofilms on a GaN/AlN heterostructure. AIP Advances, 2014, 4, 107123.	1.3	11
110	Two-step method for the deposition of AlN by radio frequency sputtering. Thin Solid Films, 2013, 545, 149-153.	1.8	17
111	Electroabsorption and refractive index modulation induced by intersubband transitions in GaN/AlN heterostructure waveguides. , 2013, , .		0
112	GaN/AlGaN waveguide quantum cascade photodetectors at Î»â€‰â‰ˆâ€‰1.55â€‰Î¼m with enhanced responsivity and â¼40â€‰GHz frequency bandwidth. Applied Physics Letters, 2013, 102, .	3.3	55
113	Photocurrent Phenomena in Nanoribbon InAlN/GaN High Electron Mobility Transistors. Japanese Journal of Applied Physics, 2013, 52, 08JE19.	1.5	0
114	All-dielectric GaN microcavity: Strong coupling and lasing at room temperature. Applied Physics Letters, 2013, 102, 101113.	3.3	52
115	Systematic study of near-infrared intersubband absorption of polar and semipolar GaN/AlN quantum wells. Journal of Applied Physics, 2013, 113, .	2.5	22
116	InGaN/GaN multipleâ€quantum well heterostructures for solar cells grown by MOVPE: case studies. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 350-354.	0.8	7
117	Environmental sensitivity of n-i-n and undoped single GaN nanowire photodetectors. Applied Physics Letters, 2013, 102, .	3.3	21
118	III-nitride semiconductors for intersubband optoelectronics: a review. Semiconductor Science and Technology, 2013, 28, 074022.	2.0	159
119	III-nitride nanostructures for optical gas detection and pH sensing. Proceedings of SPIE, 2013, , .	0.8	4
120	Measuring the refractive index around intersubband transition resonance in GaN/AlN multi quantum wells. Optics Express, 2013, 21, 3800.	3.4	6
121	Waveguide saturable absorbers at 155 Î¼m based on intraband transitions in GaN/AlN QDs. Optics Express, 2013, 21, 27578.	3.4	16
122	Polarization fields in GaN/AlN nanowire heterostructures studied by off-axis holography. Journal of Physics: Conference Series, 2013, 471, 012019.	0.4	4
123	AlGaN/AlN quantum dots for UV light emitters. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 285-288.	0.8	11
124	Terahertz absorbing AlGaN/GaN multi-quantum-wells: Demonstration of a robust 4-layer design. Applied Physics Letters, 2013, 103, 091108.	3.3	27
125	Single GaN-Based Nanowires for Photodetection and Sensing Applications. Japanese Journal of Applied Physics, 2013, 52, 11NG01.	1.5	12
126	Photovoltaic Response of InGaN/GaN Multiple-Quantum Well Solar Cells. Japanese Journal of Applied Physics, 2013, 52, 08JH05.	1.5	22

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127	InGaN/GaN quantum dots as optical probes for the electric field at the GaN/electrolyte interface. Journal of Applied Physics, 2013, 114, 074313.	2.5	4
128	GaN-based nanowire photodetectors. Proceedings of SPIE, 2012, , .	0.8	2
129	Electroabsorption and refractive index modulation induced by intersubband transitions in GaN/AlN multiple quantum wells. Optics Express, 2012, 20, 12541.	3.4	13
130	Coupling of intersubband transitions to zone-folded acoustic phonons in a GaN/AlN superlattice. Physical Review B, 2012, 85, .	3.2	4
131	Correlated Structural, Electronic, and Optical Properties of AlN/GaN Multiple Quantum Disks in GaN Nanowires. Applied Physics Express, 2012, 5, 025001.	2.4	6
132	Highly spatially resolved Cathodoluminescence of Single GaN Quantum Dots directly performed in a Scanning Transmission Electron Microscope. Microscopy and Microanalysis, 2012, 18, 1878-1879.	0.4	2
133	Thermal stability of the deep ultraviolet emission from AlGaN/AlN Stranski-Krastanov quantum dots. Applied Physics Letters, 2012, 101, .	3.3	22
134	Resonant Tunneling Transport in a GaN/AlN Multiple-Quantum-Well Structure. Applied Physics Express, 2012, 5, 052203.	2.4	17
135	Room-Temperature Photodetection Dynamics of Single GaN Nanowires. Nano Letters, 2012, 12, 172-176.	9.1	139
136	Carrier localization in InN/InGaN multiple-quantum wells with high In-content. Applied Physics Letters, 2012, 101, 062109.	3.3	20
137	Correlation of Polarity and Crystal Structure with Optoelectronic and Transport Properties of GaN/AlN/GaN Nanowire Sensors. Nano Letters, 2012, 12, 5691-5696.	9.1	73
138	Structure and strain state of polar and semipolar InGaN quantum dots. Applied Surface Science, 2012, 260, 7-12.	6.1	7
139	Morphology and origin of V-defects in semipolar (11â€“22) InGaN. Journal of Crystal Growth, 2012, 339, 1-7.	1.5	10
140	III-nitride intersubband photonics. Proceedings of SPIE, 2012, , .	0.8	0
141	Infrared photoluminescence of high Inâ€content InN/InGaN multipleâ€quantumâ€wells. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 17-20.	1.8	4
142	Responsivity and photocurrent dynamics in single GaN nanowires. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 642-645.	0.8	6
143	Structural properties of semipolar InGaN/GaN quantum dot superlattices grown by plasma-assisted MBE. Microelectronic Engineering, 2012, 90, 108-111.	2.4	8
144	Improvement of InN layers deposited on Si(111) by RF sputtering using a low-growth-rate InN buffer layer. Thin Solid Films, 2012, 520, 2805-2809.	1.8	16

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145	Femto-second electron transit time characterization in GaN/AlGaN quantum cascade detector at 1.5 micron. Applied Physics Letters, 2011, 99, .	3.3	32
146	Intersubband spectroscopy probing higher order interminiband transitions in AlN-GaN-based superlattices. Applied Physics Letters, 2011, 98, 071104.	3.3	5
147	Bragg polariton luminescence from a GaN membrane embedded in all dielectric microcavity. Applied Physics Letters, 2011, 98, 221101.	3.3	10
148	Internal quantum efficiency of III-nitride quantum dot superlattices grown by plasma-assisted molecular-beam epitaxy. Journal of Applied Physics, 2011, 109, 103501.	2.5	63
149	III-nitride semiconductors for intersubband devices. , 2011, , .		1
150	Strain relaxation in GaN/Al0.1Ga0.9N superlattices for mid-infrared intersubband absorption. Journal of Crystal Growth, 2011, 323, 64-67.	1.5	6
151	Highâ€surfaceâ€quality nanocrystalline InN layers deposited on GaN templates by RF sputtering. Physica Status Solidi (A) Applications and Materials Science, 2011, 208, 65-69.	1.8	6
152	Growth and characterization of polar (0001) and semipolar (11â¯22) InGaN/GaN quantum dots. Journal of Crystal Growth, 2011, 323, 161-163.	1.5	11
153	Strong suppression of internal electric field in GaN/AlGaN multi-layer quantum dots in nanowires. Applied Physics Letters, 2011, 99, .	3.3	20
154	Nonlinear absorption of InN/InGaN multiple-quantum-well structures at optical telecommunication wavelengths. Applied Physics Letters, 2011, 98, .	3.3	27
155	Improved luminescence and thermal stability of semipolar (11-22) InGaN quantum dots. Applied Physics Letters, 2011, 98, 201911.	3.3	19
156	Strain relaxation in GaN/AlxGa1-xN superlattices grown by plasma-assisted molecular-beam epitaxy. Journal of Applied Physics, 2011, 110, .	2.5	29
157	Si-interdiffusion in heavily doped AlN-GaN-based quantum well intersubband photodetectors. Applied Physics Letters, 2011, 98, 241101.	3.3	4
158	Investigation of the negative differential resistance reproducibility in AlN/GaN double-barrier resonant tunnelling diodes. Applied Physics Letters, 2011, 99, 182109.	3.3	34
159	Photocurrent characterization of intraband transition in GaNVAlN quantum dots. Journal of Physics: Conference Series, 2010, 245, 012068.	0.4	0
160	Polar and semipolar III-nitrides for long wavelength intersubband devices. Proceedings of SPIE, 2010, , .	0.8	4
161	Performance improvement of AlN/GaN-based intersubband detectors thanks to quantum dot active regions. Proceedings of SPIE, 2010, , .	0.8	0
162	Intersubband Transition-Based Processes and Devices in AlN/GaN-Based Heterostructures. Proceedings of the IEEE, 2010, 98, 1234-1248.	21.3	40

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163	Influence of deposition conditions on nanocrystalline InN layers synthesized on Si(111) and GaN templates by RF sputtering. Journal of Crystal Growth, 2010, 312, 2689-2694.	1.5	13
164	GaN/AlGaN nanostructures for intersubband optoelectronics. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 1421-1424.	1.8	4
165	GaN/AlN quantum disc singleâ€nanowire photodetectors. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 1323-1327.	1.8	10
166	Interfacial structure of semipolar AlN grown on m -plane sapphire by MBE. Physica Status Solidi (B): Basic Research, 2010, 247, 1637-1640.	1.5	14
167	Intersubband optics in GaN-based nanostructures - physics and applications. Physica Status Solidi (B): Basic Research, 2010, 247, 1622-1627.	1.5	12
168	Novel InN/InGaN multiple quantum well structures for slow-light generation at telecommunication wavelengths. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 100-103.	0.8	1
169	The microstructure and properties of InN layers. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 1301-1304.	0.8	10
170	Pâ€type doping of semipolar GaN(11$ ar 2 $2) by plasmaâ€assisted molecularâ€beam epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 1913-1915.	0.8	6
171	Effect of doping on the mid-infrared intersubband absorption in GaN/AlGaN superlattices grown on Si(111) templates. Applied Physics Letters, 2010, 96, .	3.3	42
172	Indium kinetics during the plasma-assisted molecular beam epitaxy of semipolar (11â^’22) InGaN layers. Applied Physics Letters, 2010, 96, 181907.	3.3	27
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